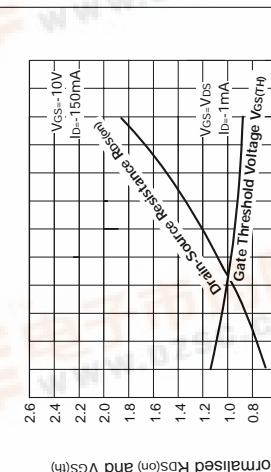
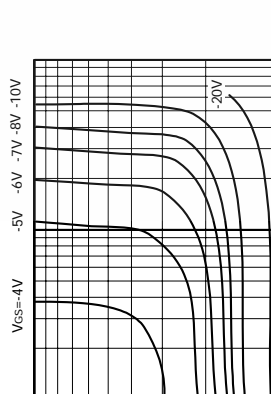
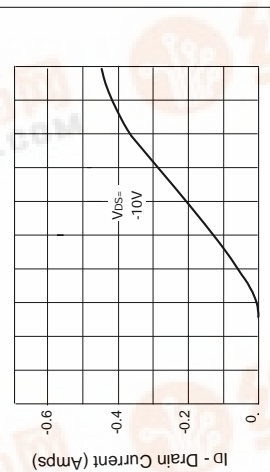
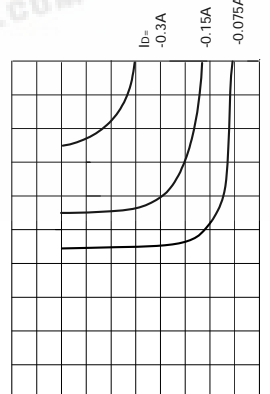
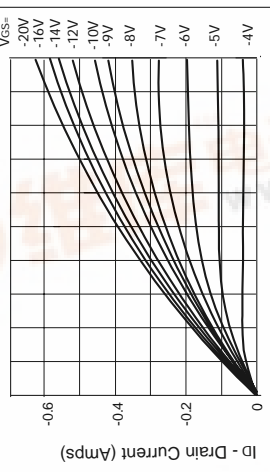
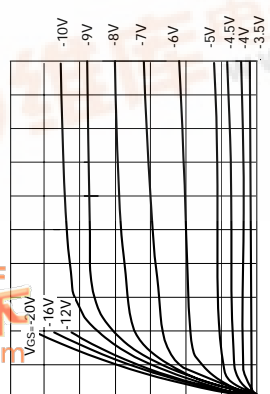




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TYPICAL CHARACTERISTICS

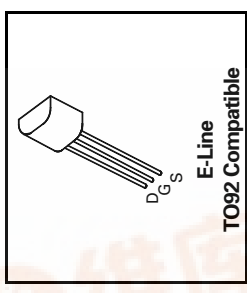


P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 100 Volt V_{DS}
- * R_{DS(on)} = 20Ω



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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V _{DS}	-100	V
Continuous Drain Current at T _{amb} =25°C	I _D	-140	mA
Pulsed Drain Current	I _{DM}	-1.2	A
Gate Source Voltage	V _{GS}	± 20	V
Power Dissipation at T _{amb} =25°C	P _{tot}	625	mW
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS
Drain-Source Breakdown Voltage	BV _{DSS}	-100		V	I _D = -1mA, V _{GS} = 0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.5	-3.5	V	I _D = -1mA, V _{DS} = V _{GS}
Gate-Body Leakage	I _{GSS}		20	nA	V _{GS} = ± 20V, V _{DS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	-1	-50	μA	V _{DS} = -100V, V _{GS} = 0
On-State Drain Current (1)	I _{D(on)}	-300		mA	V _{DS} = -80V, V _{GS} = 0V, T = 125°C (2)
Static Drain-Source On-State Resistance (1)	R _{DS(on)}		20	Ω	V _{DS} = -25 V, V _{GS} = -10V
Forward Transconductance (1)(2)	g _{fs}	50		mS	V _{DS} = -25V, I _D = -150mA
Input Capacitance (2)	C _{iss}		50	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1MHz
Common Source Output Capacitance (2)	C _{oss}		15	pF	
Reverse Transfer Capacitance (2)	C _{rss}		5	pF	
Turn-On Delay Time (2)(3)	t _{d(on)}		8	ns	
Rise Time (2)(3)	t _r		8	ns	
Turn-Off Delay Time (2)(3)	t _{d(off)}		8	ns	V _{DD} = -25V, I _D = -150mA
Fall Time (2)(3)	t _f		8	ns	

(1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤ 2%
 (2) Sample test.

P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

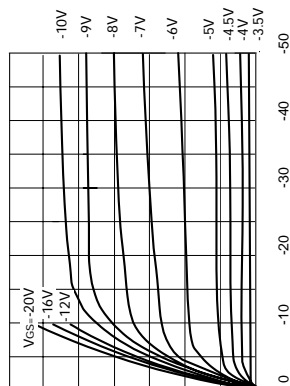
ISSUE 2 – MARCH 94

FEATURES

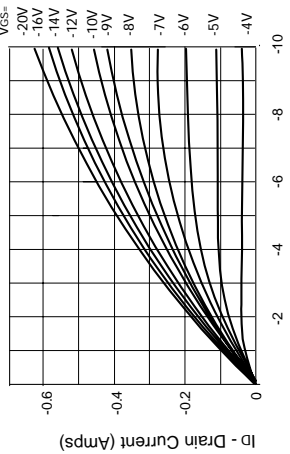
- * 100 Volt V_{DS}
- * $R_{DS(on)}=20\Omega$

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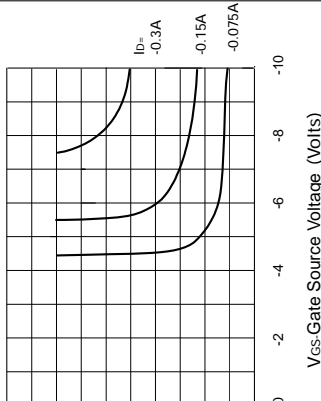
TYPICAL CHARACTERISTICS



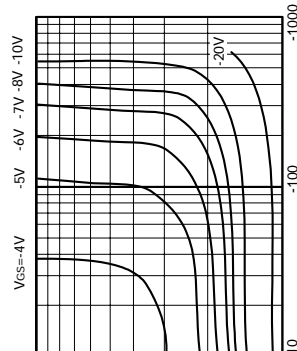
Output Characteristics



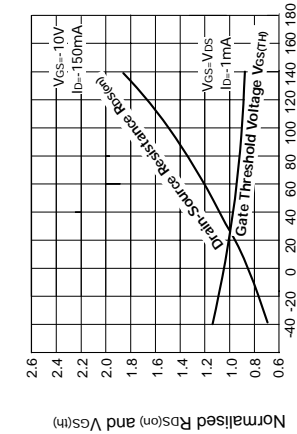
Saturation Characteristics



Voltage Saturation Characteristics

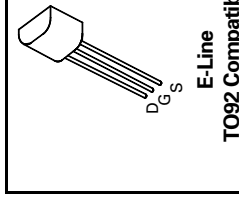


On-resistance v drain current



Transfer Characteristics

Normalised $R_{DS(on)}$ and $V_{GS(th)}$ v Temperature



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-100	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	-140	mA
Pulsed Drain Current	I_{DM}	-1.2	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	625	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-100		V	$I_D=-1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-3.5	V	$I_D=-1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		-1	μA	$V_{DS}=-100V, V_{GS}=0$
On-State Drain Current (1)	$I_{D(on)}$	-300		mA	$V_{DS}=-80V, V_{GS}=0V, T=125^{\circ}C(2)$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		20	Ω	$V_{DS}=-25V, V_{GS}=-10V$
Forward Transconductance (1)(2)	g_{fs}	50		mS	$V_{DS}=-25V, I_D=-150mA$
Input Capacitance (2)	C_{iss}		50	pF	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		15	pF	
Reverse Transfer Capacitance (2)	C_{rss}		5	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		8	ns	
Rise Time (2)(3)	t_r		8	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		8	ns	$V_{DD}=-25V, I_D=-150mA$
Fall Time (2)(3)	t_f		8	ns	

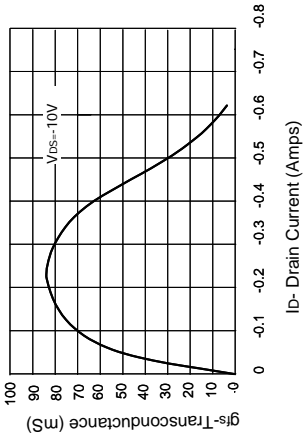
(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

(2) Sample test.

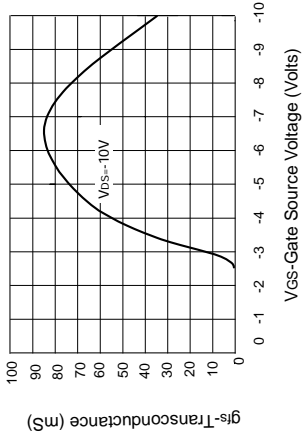
Switching times measured with 50 Ω source impedance and $\pm 5ns$ rise time on a pulse generator

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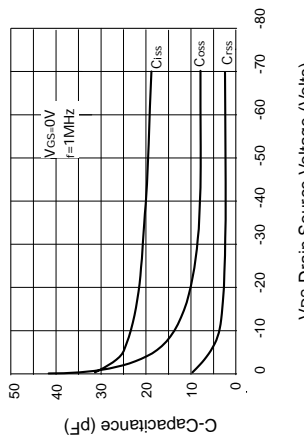
TYPICAL CHARACTERISTICS



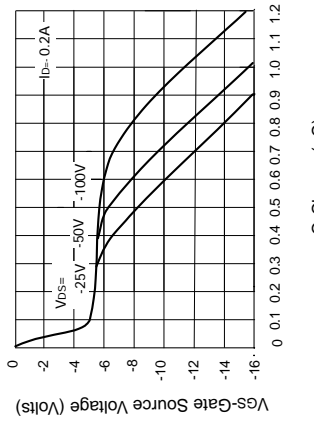
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage